

Silicon NPN Power Transistors

2SC1046

DESCRIPTION

- With TO-3 package
- High breakdown voltage

APPLICATIONS

- For CRT horizontal output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

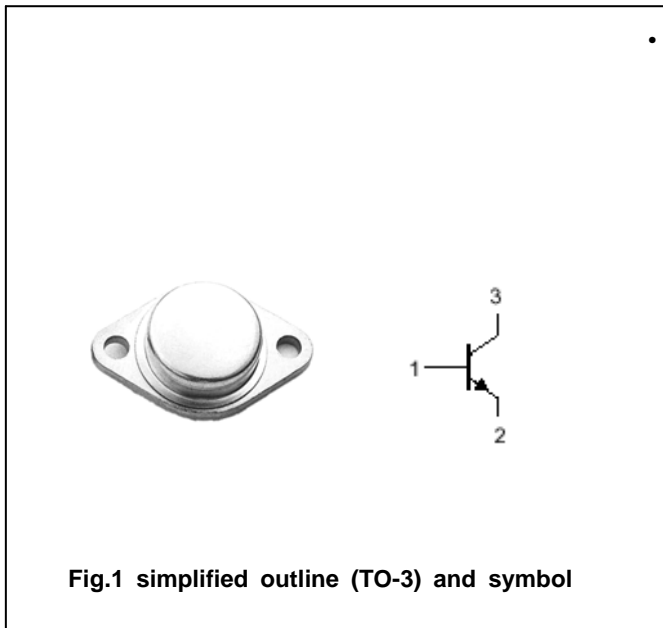


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1000	V
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		3	A
P _C	Collector power dissipation	T _C =25°C	25	W
T _j	Junction temperature		125	°C
T _{stg}	Storage temperature		-40~125	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =5mA; I _B =0	400			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA; I _E =0	1000			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2 A; I _B =0.4A			2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =800V; I _E =0			10	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μ A
h _{FE}	DC current gain	I _C =2 A ; V _{CE} =5V	4		20	

PACKAGE OUTLINE

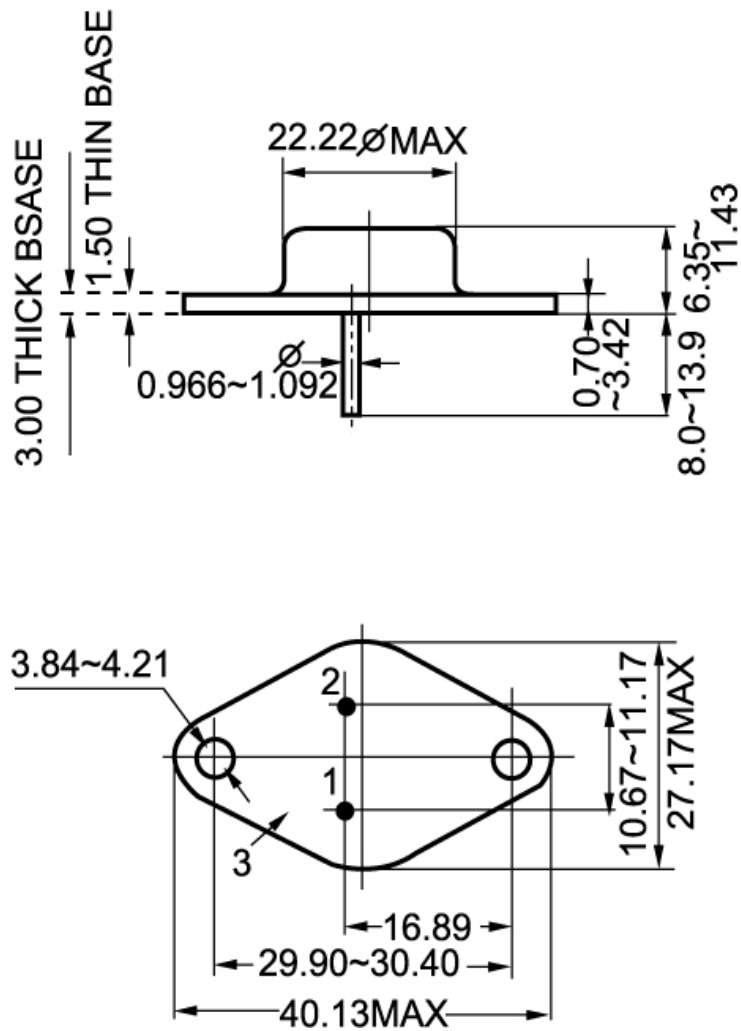


Fig.2 Outline dimensions